

# Fast recovery diode

## RF073M2S

### ●Applications

High frequency rectification

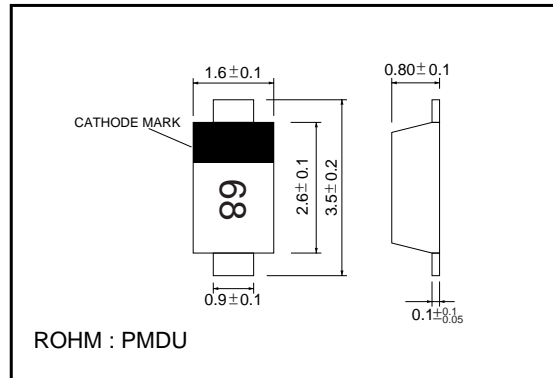
### ●Features

- 1) Small power mold type (PMDS)
- 2) Ultra low  $V_F$
- 3) Very fast recovery
- 4) Low switching loss

### ●Construction

Silicon epitaxial planar

### ●External dimensions (Unit : mm)



### ●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Reverse voltage (repetitive peak)	$V_{RM}$	200	V
Reverse voltage (DC)	$V_R$	200	V
Forward voltage (DC)	$I_F$ *	1.0	A
Average rectified forward current	$I_o$ *	0.7	A
Forward peak surge current (60Hz · 1cyc.)	$I_{FSM}$	15	A
Junction temperature	$T_j$	150	°C
Storage temperature	$T_{stg}$	-55 to +150	°C

\*  $T_c$  max=120°C Mounting on glass epoxy board

### ●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	$V_F$	-	0.830	0.890	V	$I_F=0.7A$
Reverse current	$I_R$	-	1.2	10	$\mu A$	$V_R=200V$
Reverse recovery time	$t_{rr}$	-	9	20	ns	$I_F=0.5A, I_R=1.0A, I_{rr}=0.25 \times I_R$

Note) ESD sensitive product handling required.

Diodes

●Electrical characteristic curves (Ta=25°C)

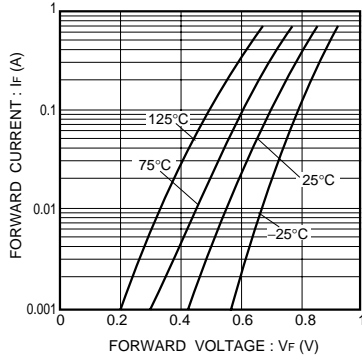


Fig.1 Forward temperature characteristics

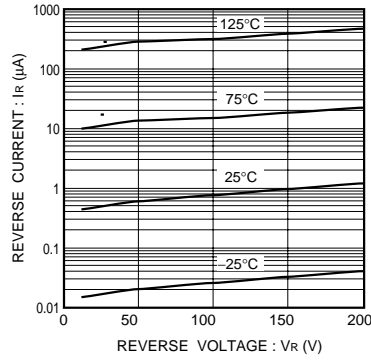


Fig.2 Reverse temperature characteristics

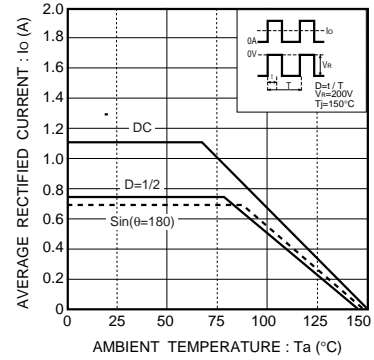


Fig.3 Derating curve

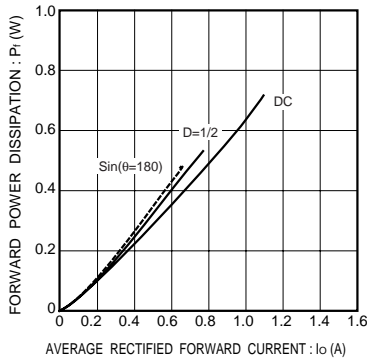


Fig. 4 Power dissipation characteristics

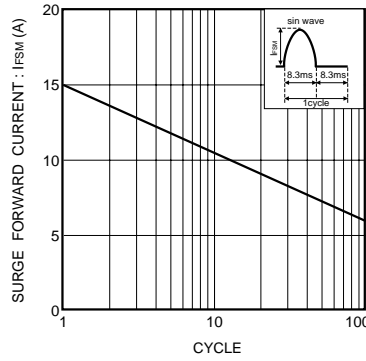


Fig.5 Forward peak surge current

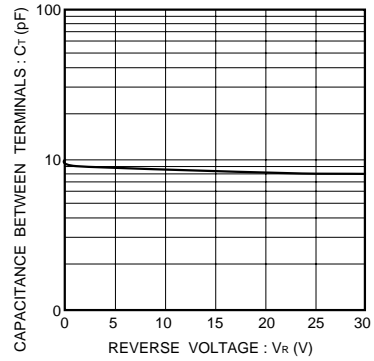


Fig. 6 Capacitance between terminals characteristics

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